

## Main Product Characteristics

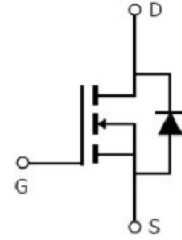
$V_{DSS}$	600V
$R_{DS(on)}$	0.8ohm(typ.)
$I_D$	10A



TO220F



Marking and Pin Assignment



Schematic Diagram

## Features and Benefits

- Advanced trench MOSFET process technology
- Special designed for PWM, load switching and general purpose applications
- Ultra low on-resistance with low gate charge
- Fast switching and reverse body recovery
- 150°C operating temperature
- Lead free product



## Description

It utilizes the latest trench processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications.

## Absolute Max Rating

Symbol	Parameter	Max.	Units
$I_D @ TC = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ <sup>①</sup>	10	A
$I_D @ TC = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ <sup>①</sup>	6	
$I_{DM}$	Pulsed Drain Current <sup>②</sup>	40	
$P_D @ TC = 25^\circ C$	Power Dissipation <sup>③</sup>	156	W
	Linear Derating Factor	1.2	W/°C
$V_{DS}$	Drain-Source Voltage	600	V
$V_{GS}$	Gate-to-Source Voltage	± 30	V
$E_{AS}$	Single Pulse Avalanche Energy @ L=14.2mH	700	mJ
$I_{AS}$	Avalanche Current @ L=14.2mH	10	A
$T_J \quad T_{STG}$	Operating Junction and Storage Temperature Range	-55 to + 150	°C

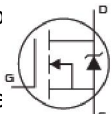
## Thermal Resistance

Symbol	Characteristics	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-case <sup>③</sup>	—	0.8	$^{\circ}C/W$
$R_{\theta JA}$	Junction-to-ambient ( $t \leq 10s$ ) <sup>④</sup>	—	62	$^{\circ}C/W$
	Junction-to-Ambient (PCB mounted, steady-state) <sup>④</sup>	—	40	$^{\circ}C/W$

## Electrical Characteristics @ $T_A=25^{\circ}C$ unless otherwise specified

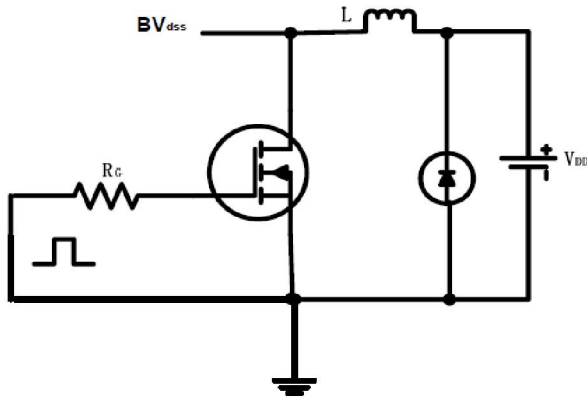
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	600	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	0.8	0.83	$\Omega$	$V_{GS}=10V, I_D = 4.75A$
		—	1.79	—		$T_J = 125^{\circ}C$
$V_{GS(th)}$	Gate threshold voltage	2	—	4	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
		—	2.1	—		$T_J = 125^{\circ}C$
$I_{DSS}$	Drain-to-Source leakage current	—	—	1	$\mu A$	$V_{DS} = 600V, V_{GS} = 0V$
		—	—	50		$T_J = 125^{\circ}C$
$I_{GSS}$	Gate-to-Source forward leakage	—	—	100	nA	$V_{GS} = 30V$
		-100	—	—		$V_{GS} = -30V$
$Q_g$	Total gate charge	—	42.1	—	nC	$I_D = 10A,$ $V_{DS}=480V,$ $V_{GS} = 10V$
$Q_{gs}$	Gate-to-Source charge	—	8.2	—		
$Q_{gd}$	Gate-to-Drain("Miller") charge	—	16.2	—		
$t_{d(on)}$	Turn-on delay time	—	20.9	—	ns	$V_{GS}=10V, V_{DS}=330V,$ $R_L=33\Omega,$ $R_{GEN}=25\Omega$ $I_D=10A$
$t_r$	Rise time	—	36.4	—		
$t_{d(off)}$	Turn-Off delay time	—	119.9	—		
$t_f$	Fall time	—	52.2	—		
$C_{iss}$	Input capacitance	—	1515	—	pF	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1MHz$
$C_{oss}$	Output capacitance	—	137	—		
$C_{rss}$	Reverse transfer capacitance	—	9	—		

## Source-Drain Ratings and Characteristics

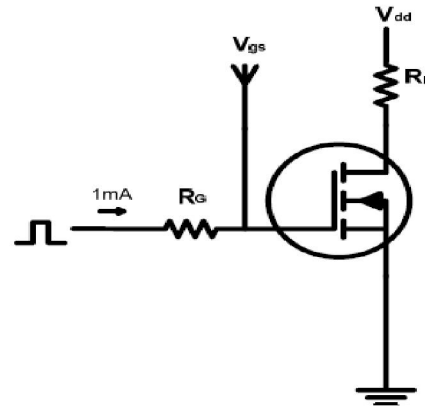
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	10	A	MOSFET symb showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode)	—	—	40	A	
$V_{SD}$	Diode Forward Voltage	—	0.90	1.3	V	$I_S=10A, V_{GS}=0V$
$t_{rr}$	Reverse Recovery Time	—	866	—	ns	$T_J = 25^{\circ}C, I_F = 10A, di/dt = 100A/\mu s$
$Q_{rr}$	Reverse Recovery Charge	—	5163	—	nC	

## Test Circuits and Waveforms

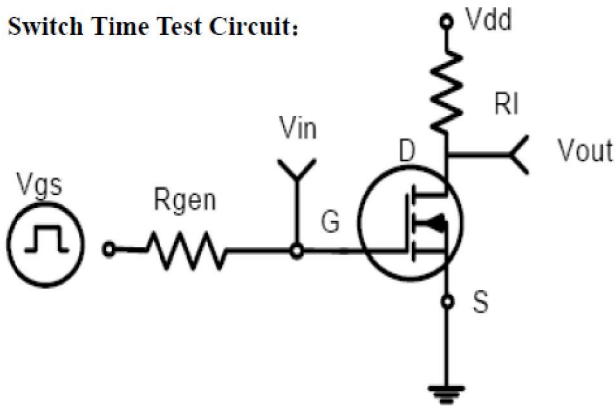
EAS test circuits:



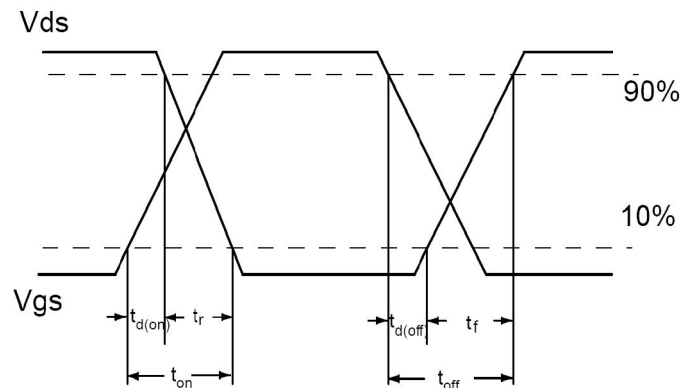
Gate charge test circuit:



Switch Time Test Circuit:



Waveforms:



### Notes:

- ① The maximum current rating is limited by bond-wires.
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.
- ④ The value of  $R_{\theta JA}$  is measured with the device mounted on 1in 2 FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^\circ\text{C}$
- ⑤ These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of  $T_{J(MAX)} = 150^\circ\text{C}$ .
- ⑥ The maximum current rating is limited by bond-wires.

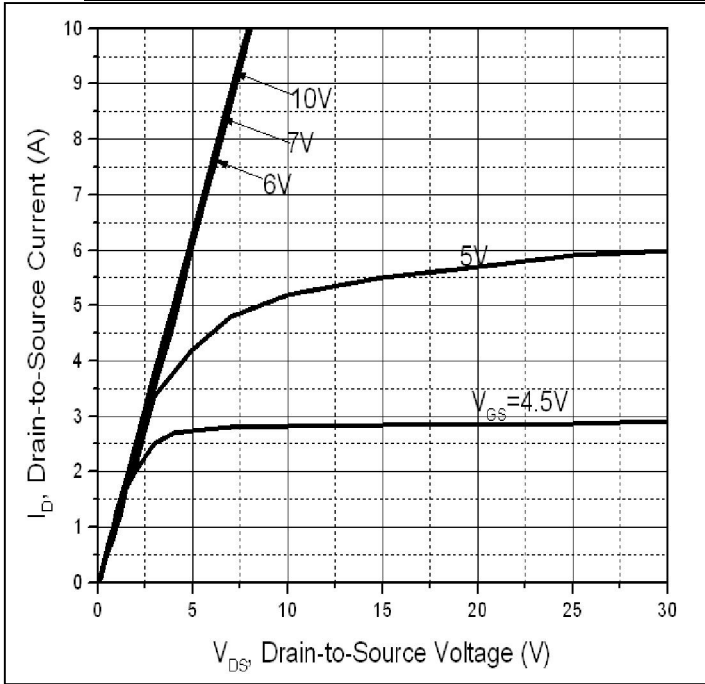


Figure 1: Typical Output Characteristics

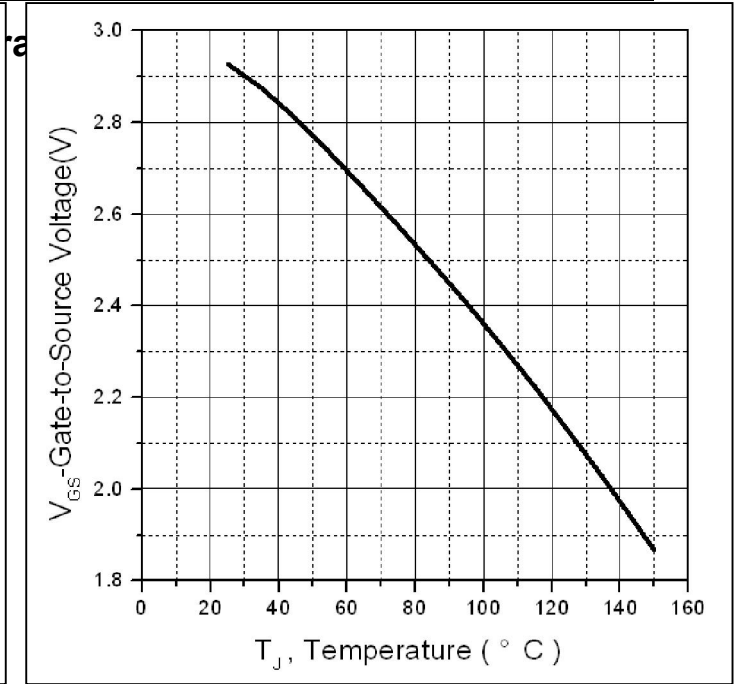


Figure 2. Gate to source cut-off voltage

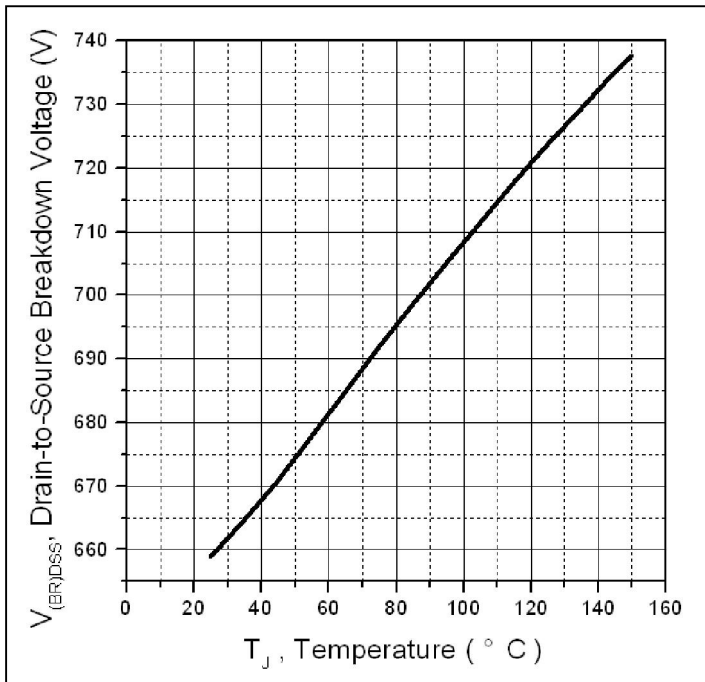


Figure 3. Drain-to-Source Breakdown Voltage vs. Temperature

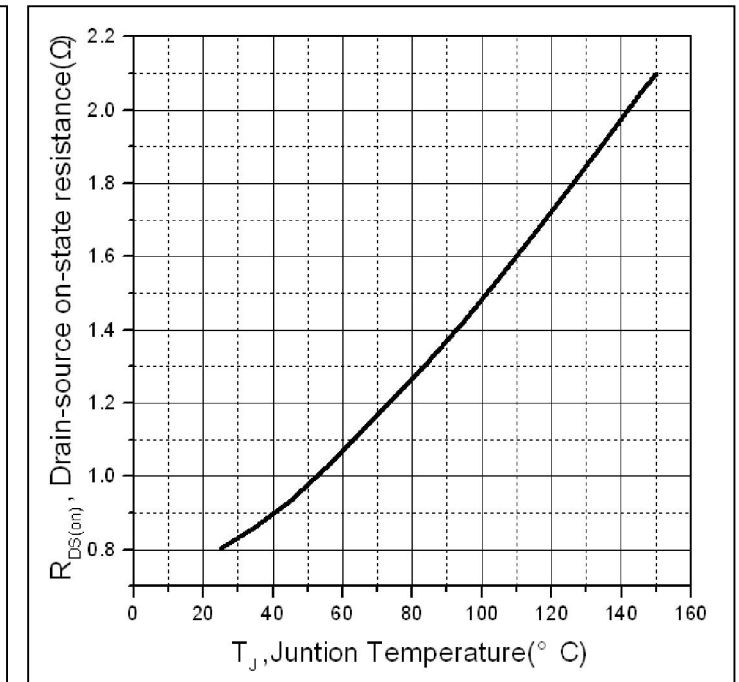


Figure 4: Normalized On-Resistance Vs. Case Temperature

## Typical Electrical and Thermal Characteristics

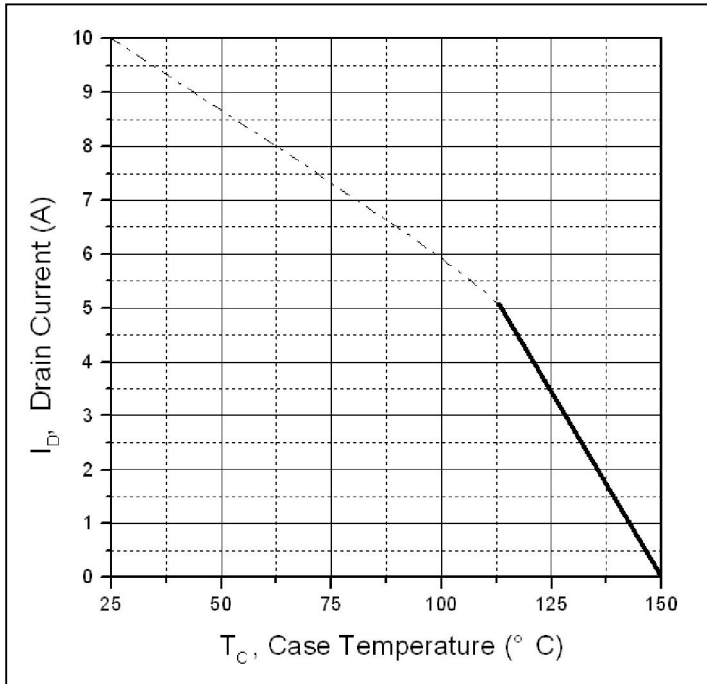


Figure 5. Maximum Drain Current Vs. Case Temperature

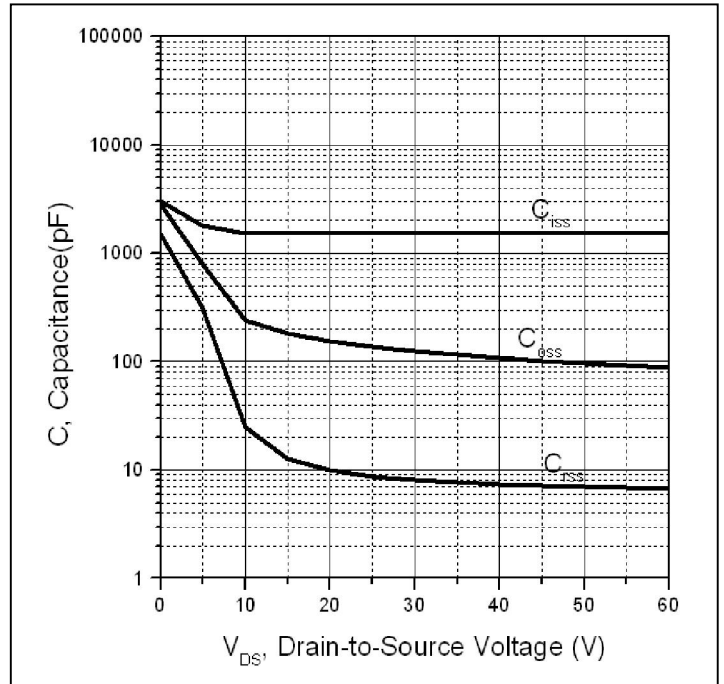


Figure 6. Typical Capacitance Vs. Drain-to-Source Voltage

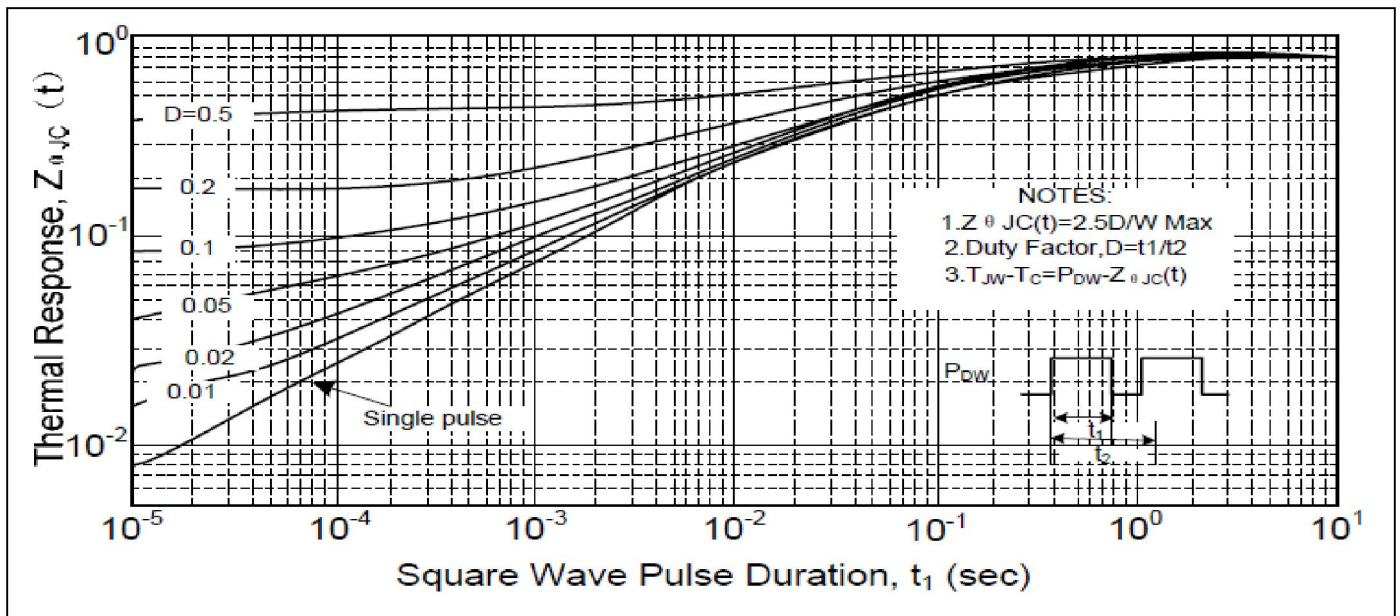
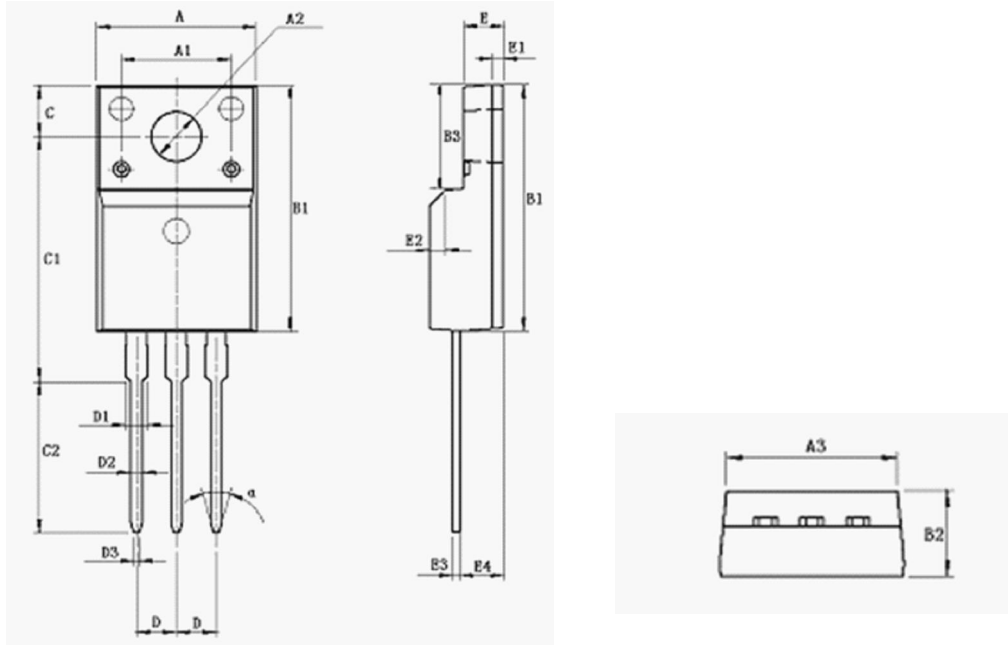


Figure 7. Maximum Effective Transient Thermal Impedance, Junction-to-Case

## Mechanical Data

TO220F PACKAGE OUTLINE DIMENSION



Symbol	Dimension In Millimeters			Dimension In Inches		
	Min	Nom	Max	Min	Nom	Max
A	9.960	10.160	10.360	0.392	0.400	0.408
A1	7.000			0.276	0.000	0.000
A2	3.080	3.180	3.280	0.121	0.125	0.129
A3	9.260	9.460	9.660	0.365	0.372	0.380
B1	15.670	15.870	16.070	0.617	0.625	0.633
B2	4.500	4.700	4.900	0.177	0.185	0.193
B3	6.480	6.680	6.880	0.255	0.263	0.271
C	3.200	3.300	3.400	0.126	0.130	0.134
C1	15.600	15.800	16.000	0.614	0.622	0.630
C2	9.550	9.750	9.950	0.376	0.384	0.392
D	2.54 (TYP)			1.00 (TYP)		
D1	-	-	1.470	-	-	0.058
D2	0.700	0.800	0.900	0.028	0.031	0.035
D3	0.250	0.350	0.450	0.010	0.014	0.018
E	2.340	2.540	2.740	0.092	0.100	0.108
E1	0.700			0.028		
E2	1.0*45 <sup>0</sup>			1.0*45 <sup>0</sup>		
E3	0.450	0.500	0.600	0.018	0.020	0.024
E4	2.560	2.760	2.960	0.101	0.109	0.117
□	30 <sup>0</sup>			30 <sup>0</sup>		



## Ordering and Marking Information

**Device Marking: SSF10N60F**

Package (Available)  
TO220F  
Operating Temperature Range  
C : -55 to 150 °C

## Devices per Unit

Package Type	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Carton Box	Units/Carton Box
TO220F	50	20	1000	6	6000

## Reliability Test Program

Test Item	Conditions	Duration	Sample Size
High Temperature Reverse Bias(HTRB)	$T_j=125^{\circ}\text{C}$ to $150^{\circ}\text{C}$ @ 80% of Max $V_{DSS}/V_{CES}/V_R$	168 hours 500 hours 1000 hours	3 lots x 77 devices
High Temperature Gate Bias(HTGB)	$T_j=150^{\circ}\text{C}$ @ 100% of Max $V_{GSS}$	168 hours 500 hours 1000 hours	3 lots x 77 devices